

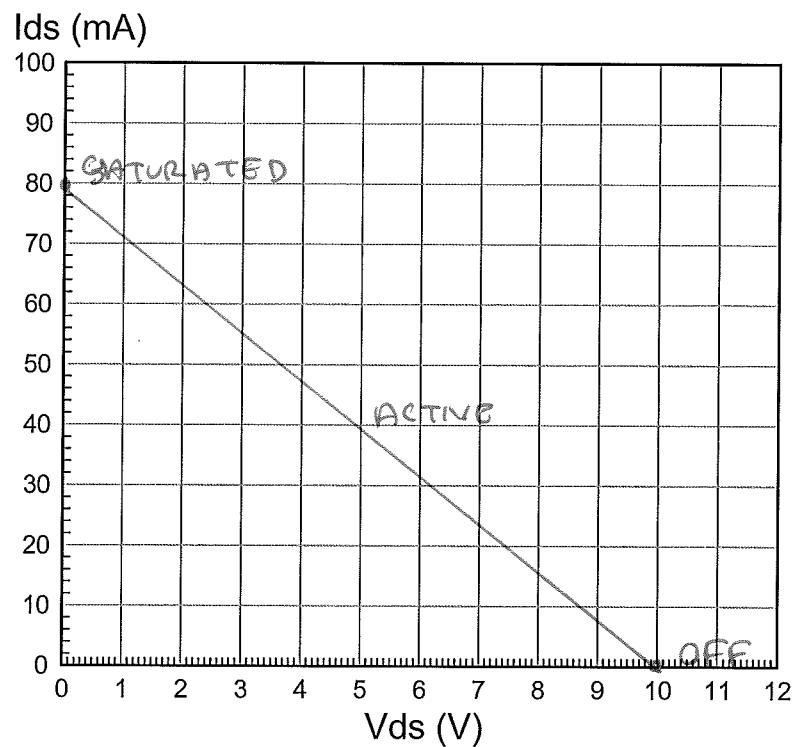
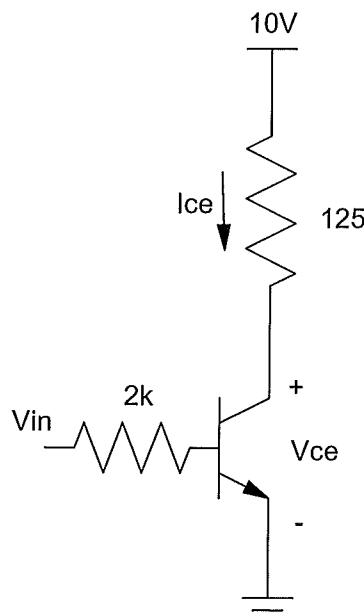
ECE 320 - Final (pt 2): Name _____

BJT, MOSFET, Op-Amps. October 30, 2015

1a) Draw the load line for the following circuit on the graph below.

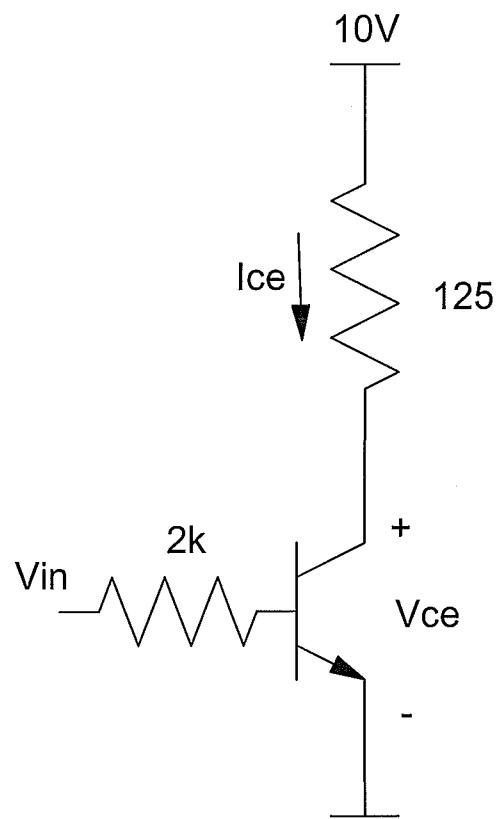
1b) Label on this graph when the BJT is

- Off
- Active
- Saturated



2) Determine the voltages and currents for the following circuit when $V_{in} = 2V$ and $V_{in} = 20V$. Assume an ideal silicon transistor with a current gain of 100.

$V_{in} = 2V$		$V_{in} = 20V$	
V_{ce}	I_{ce}	V_{ce}	I_{ce}
1.875V	65mA	0.2V	78.4mA

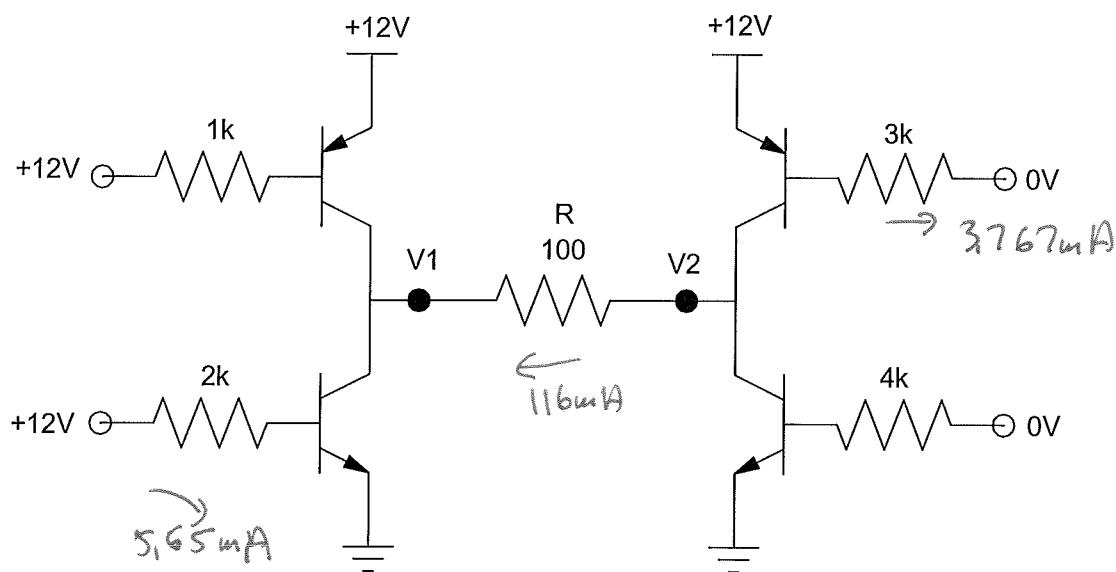


$$I_b = \frac{2 - 0.7}{2k} = 65\mu A$$

$$I_c = \beta I_b = 65mA$$

- 3) BJT H-Bridge. Determine the voltages at each node. Also determine the smallest R can be while keeping the BJT's off or saturated. Assume an ideal silicon transistor with a current gain of 100.

V1	V2	Smallest Allowable Value of R
0.2V	11.8V	30.8Ω

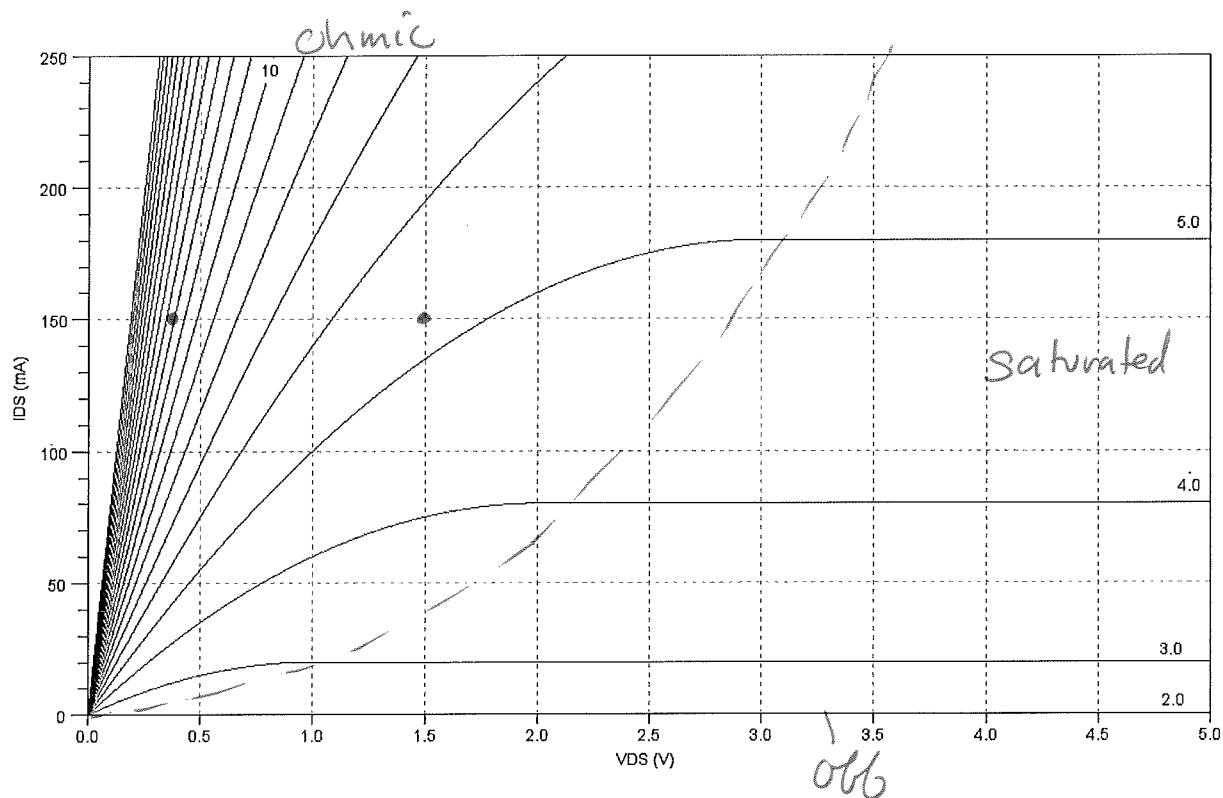


$$\text{max} = 376.7 \text{ mA}$$

$$R = \frac{11.6V}{376 \text{ mA}} = 30.8 \Omega$$

- 4) The V/I characteristics for a MOSFET is shown below with $V_t = 2V$ and $2V < V_{gs} < 20$ (plotted every 1V for V_{gs}). Determine the following:

Label the regions (Off - Ohmic - Saturated)	K_n	V_{gs} for $R_{ds} = 2 \text{ Ohms}$ at $I_{ds} = 150\text{mA}$	V_{gs} for $R_{ds} = 10 \text{ Ohms}$ at $I_{ds} = 150\text{mA}$
on graph	.04	14.65V	5.25V



$$180\text{mA} = \frac{K_n}{2} (5 - 2)^2$$

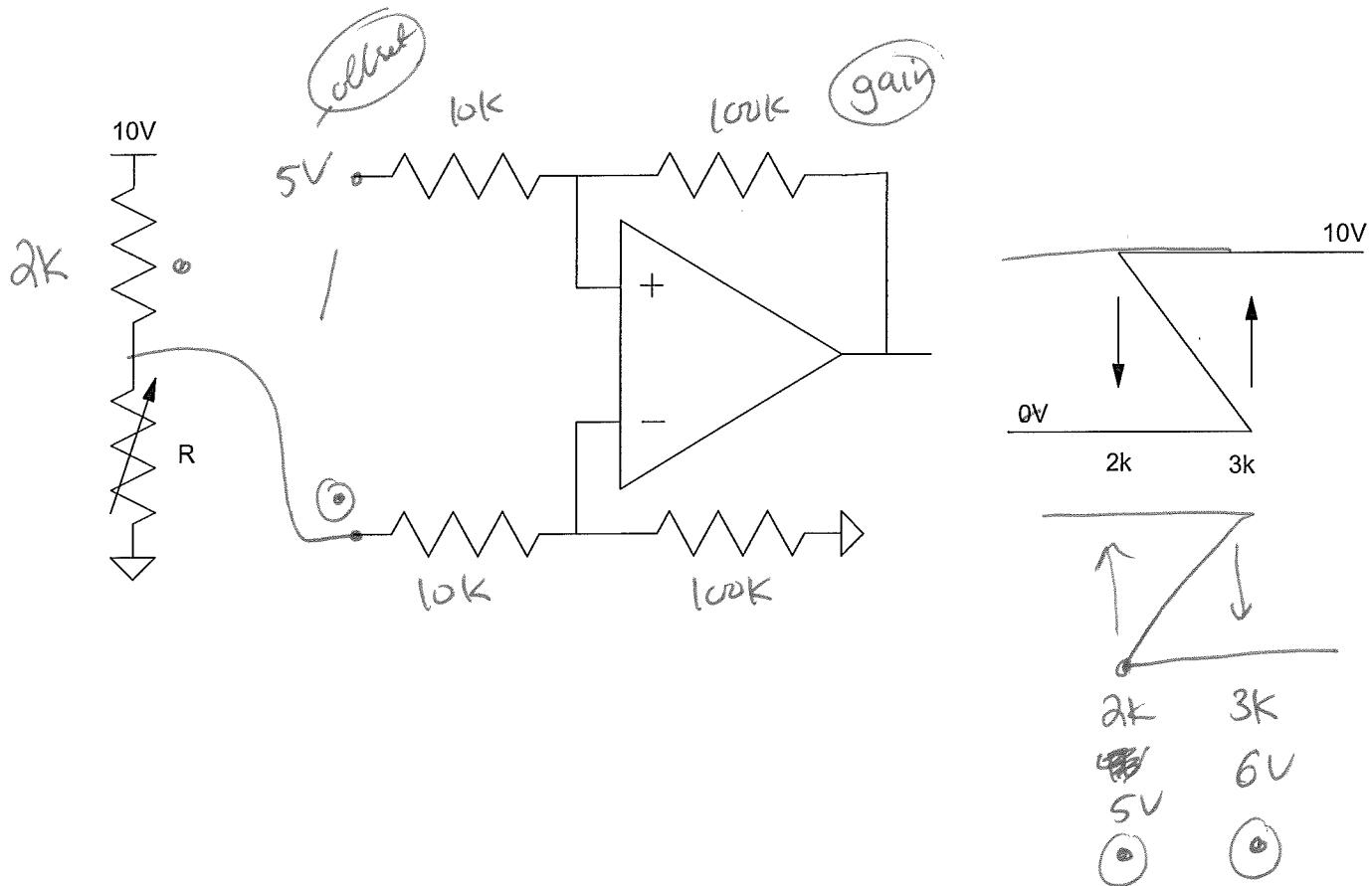
$$K_n = .04$$

$$I_{ds} = K_n \left(V_{gs} - V_t - \frac{V_{ds}}{2} \right) V_{ds}$$

$$V_{gs} = \frac{.04 \cdot 1}{.04 \cdot (.015)(2)} + \frac{.15 \cdot 2^2}{2} + 2$$

5) Design a Schmitt Trigger which outputs

- +10V when $R < 2k$ Ohms and
- 0V when $R > 3k$ Ohms



Bonus! In 2012, Steven Colbert ran attack adds against Mitt Romney, accusing him of being a mass murderer. What was the basis for this accusation?